

AMENDMENTS TO THE SPECIFICATION:

Please replace the Title with the following replacement Title:

--COMPONENT INCLUDING A FIXED ELEMENT THAT IS IN A SILICON LAYER AND IS MECHANICALLY CONNECTED TO A SUBSTRATE VIA AN ANCHORING ELEMENT AND METHOD FOR ITS MANUFACTURE--.

Please replace the paragraph beginning on page 8, line 4 of the Substitute Specification with the following replacement paragraph:

--A diaphragm layer 14 made of polysilicon or SiGe, for example, may then be produced on top of patterned second sacrificial layer 11. Following the application of a starting layer, polysilicon may simply be grown epitaxially ~~epitactically~~. Subsequently, diaphragm layer 14 may be patterned, which in the case of a polysilicon layer may also be achieved by trench etching. On the one hand, this patterning may produce openings 15 for the sacrificial layer etching, during which at least second sacrificial layer 11 and possibly also first sacrificial layer 3 may be removed. On the other hand, the patterning of diaphragm layer 14 may produce openings 16, which electrically insulate the contact lead-throughs between functional silicon layer 2 and diaphragm layer 14 in the area of contact holes 9 from the remaining areas of diaphragm layer 14. These openings 16 are referred to below as insulating trenches. Sensor element 1 featuring the diaphragm layer patterned in this manner is represented in Fig. 4.--.